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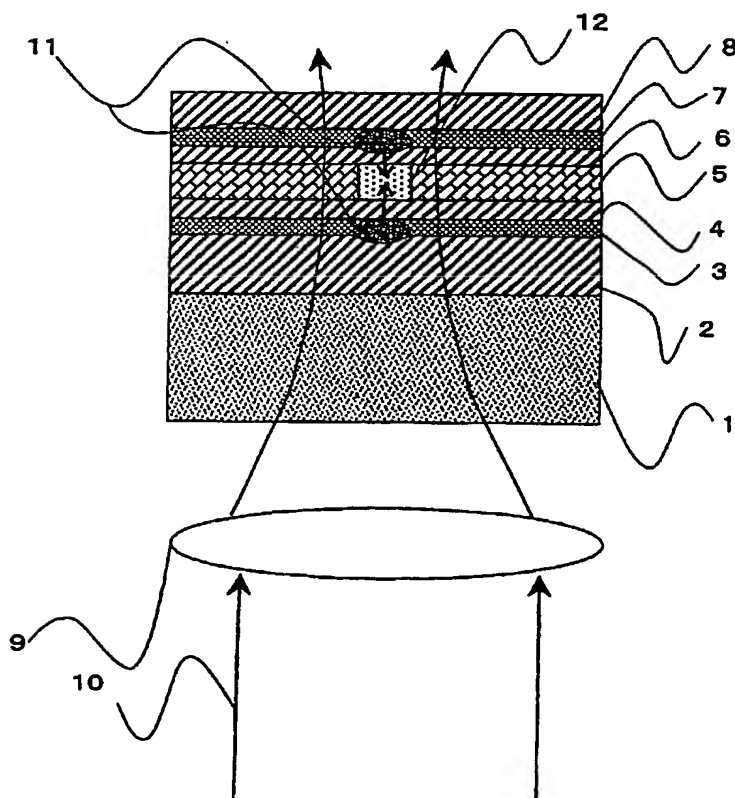
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(54) Title: **PATTERN FORMING MATERIALS AND PATTERN FORMATION METHOD USING THE MATERIALS**



(57) Abstract: Provided are pattern forming materials including a thermal sensitive material layer formed on a target substrate, a first light-to-heat converting layer formed between the thermal sensitive material layer and the target substrate, and a second light-to-heat converting layer formed on a surface of the thermal sensitive material layer opposite to the first light-to-heat converting layer, the thermal sensitive material layer being interposed between the first and second light-to-heat converting layers. A higher aspect ratio fine pattern can be formed in the thermal sensitive material layer made of photoresist using heat generated in the first and second light-to-heat converting layers formed on both surfaces of the thermal sensitive material layer.

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